

LM4250

High Reliability

Programmable Operational Amplifier

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GENERAL DESCRIPTION

The 4250 is an extremely versatile programmable monolithic operational amplifier. A single external master bias current setting resistor programs the input bias current, input offset current, quiescent power consumption, slew rate, input noise, and the gain-bandwidth product.

RESISTOR BIASING

Set Current Setting Resistor to V_S

V_S	I _{SET}				
	0.1 μ A	0.5 μ A	1.0 μ A	5 μ A	10 μ A
$\pm 1.5V$	25.6 M Ω	5.04 M Ω	2.5 M Ω	492 k Ω	244 k Ω
$\pm 3.0V$	55.6 M Ω	11.0 M Ω	5.5 M Ω	1.09 M Ω	544 k Ω
$\pm 6.0V$	116 M Ω	23.0 M Ω	11.5 M Ω	2.29 M Ω	1.14 M Ω
$\pm 9.0V$	176 M Ω	35.0 M Ω	17.5 M Ω	3.49 M Ω	1.74 M Ω
$\pm 12.0V$	236 M Ω	47.0 M Ω	23.5 M Ω	4.69 M Ω	2.34 M Ω
$\pm 1.50V$	296 M Ω	59.0 M Ω	29.5 M Ω	5.89 M Ω	2.94 M Ω

FEATURES

- $\pm 1V$ to $\pm 18V$ Power Supply Operation
- 3 nA Input Offset Current
- Standby Power Consumption as Low as 500 nW
- No Frequency Compensation Required
- Programmable Electrical Characteristics
- Offset Voltage Nulling Capability
- Can be Powered by Two Flashlight Batteries
- Short Circuit Protection

ORDERING INFORMATION

Part Number	Temperature Range	Package
LM4250 J	-55°C to +125°C	8 Lead CERDIP
LM4250 H	-55°C to +125°C	TO-99 CAN

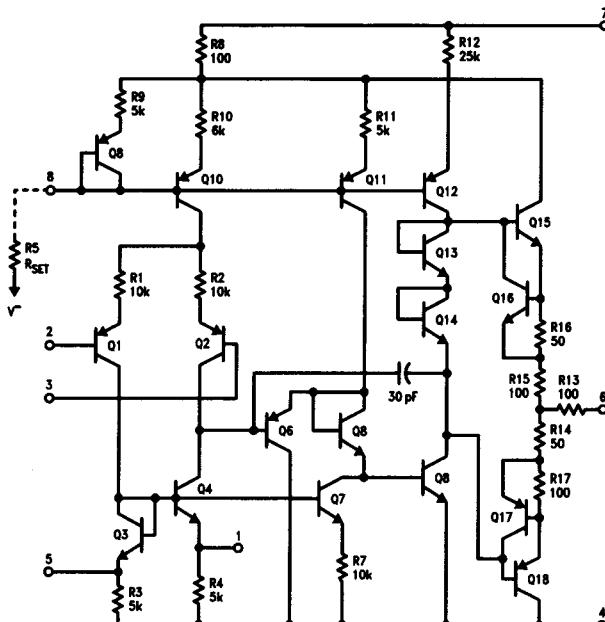


Figure 1: Functional Diagram

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LM4250**ABSOLUTE MAXIMUM RATINGS**

Supply Voltage	$\pm 18V$
Power Dissipation (Note 1)	500 mW
Differential Input Voltage	$\pm 30V$
Input Voltage (Note 2)	$\pm 15V$
ISET Current	150 μA
Operating Temperature Range	-55°C to +125°C

Output Short Circuit DurationIndefinite
 Storage Temperature Range-65°C to +150°C
 Lead Temperature (Soldering, 10 sec.)+300°C

NOTE: Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions above those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

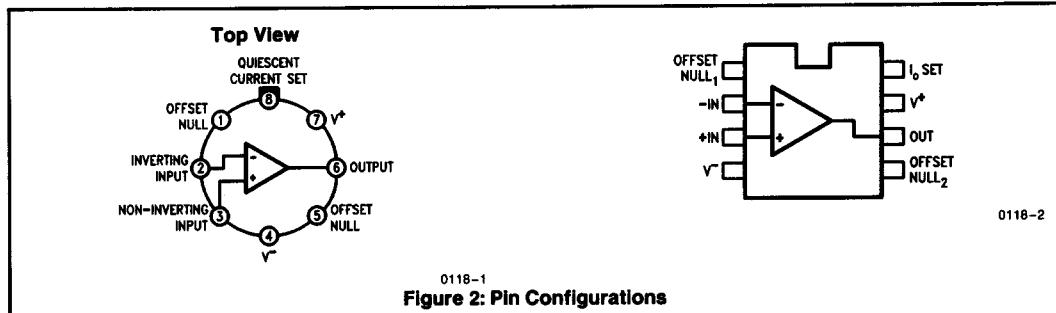


Figure 2: Pin Configurations

ELECTRICAL CHARACTERISTICS (0°C ≤ T_A ≤ +70°C unless otherwise specified)

Parameters	Conditions	V _S = ± 1.5V			
		I _{SET} = 1 μA		I _{SET} = 10 μA	
		Min	Max	Min	Max
V _{os}	T _A = 25°C, R _S ≤ 100 kΩ		5 mV		6 mV
I _{os}	T _A = 25°C		6 nA		20 nA
I _{bias}	T _A = 25°C		10 nA		75 nA
Large Signal Voltage Gain	T _A = 25°C, R _L = 100 kΩ V _O = ± 0.6V, R _L = 10 kΩ	25k		25k	
Supply Current	T _A = 25°C		8 μA		90 μA
Power Consumption	T _A = 25°C		24 μW		270 μW
V _{OS}	R _S ≤ 10 kΩ		6.5 mV		7.5 mV
I _{os}			8 nA		25 nA
I _{bias}			10 nA		80 nA
Input Voltage Range		±0.6V		±0.6V	
Large Signal Voltage Gain	V _O = ± 0.6V, R _L = 100 kΩ R _L = 10 kΩ	25k		25k	
Output Voltage Swing	R _L = 100 kΩ R _L = 10 kΩ	±0.6V		±0.6V	
Common Mode Rejection Ratio	R _S ≤ 10 kΩ	70 dB		70 dB	
Supply Voltage Rejection Ratio	R _S ≤ 10 kΩ	65 dB		65 dB	
Supply Current			8 μA		90 μA
Power Consumption			24 μW		270 μW

ELECTRICAL CHARACTERISTICS ($0^{\circ}\text{C} \leq T_A \leq +70^{\circ}\text{C}$ unless otherwise specified) (Continued)

Parameters	Conditions	$V_S = \pm 15\text{V}$			
		$I_{SET} = 1 \mu\text{A}$		$I_{SET} = 10 \mu\text{A}$	
		Min	Max	Min	Max
V_{OS}	$T_A = 25^{\circ}\text{C}, R_S \leq 100 \text{k}\Omega$		5 mV		6 mV
I_{OS}	$T_A = 25^{\circ}\text{C}$		6 nA		20 nA
I_{bias}	$T_A = 25^{\circ}\text{C}$		10 nA		75 nA
Large Signal Voltage Gain	$T_A = 25^{\circ}\text{C}, R_L = 100 \text{k}\Omega$ $V_O = \pm 0.6\text{V}, R_L = 10 \text{k}\Omega$	60k		60k	
Supply Current	$T_A = 25^{\circ}\text{C}$		11 μA		100 μA
Power Consumption	$T_A = 25^{\circ}\text{C}$		330 μW		3 mW
V_{OS}	$R_S \leq 10 \text{k}\Omega$		6.5 mV		7.5 mV
I_{OS}			8 nA		25 nA
I_{bias}			10 nA		80 nA
Input Voltage Range		$\pm 13.5\text{V}$		$\pm 13.5\text{V}$	
Large Signal Voltage Gain	$V_O = \pm 10\text{V}, R_L = 100 \text{k}\Omega$ $R_L = 10 \text{k}\Omega$	50k		50k	
Output Voltage Swing	$R_L = 100 \text{k}\Omega$ $R_L = 10 \text{k}\Omega$	$\pm 12\text{V}$		$\pm 12\text{V}$	
Common Mode Rejection Ratio	$R_S \leq 10 \text{k}\Omega$	70 dB		70 dB	
Supply Voltage Rejection Ratio	$R_S \leq 10 \text{k}\Omega$	74 dB		74 dB	
Supply Current			11 μA		100 μA
Power Consumption			300 μW		3 mW

LM4250**ELECTRICAL CHARACTERISTICS** ($-55^{\circ}\text{C} \leq T_A \leq +125^{\circ}\text{C}$ unless otherwise specified)

Parameters	Conditions	$V_S = \pm 1.5\text{V}$			
		$I_{SET} = 1 \mu\text{A}$		$I_{SET} = 10 \mu\text{A}$	
		Min	Max	Min	Max
V_{OS}	$T_A = 25^{\circ}\text{C}, R_S \leq 100 \text{k}\Omega$		6 mV		6 mV
I_{OS}	$T_A = 25^{\circ}\text{C}$		6 nA		20 nA
I_{bias}	$T_A = 25^{\circ}\text{C}$		10 nA		75 nA
Large Signal Voltage Gain	$T_A = 25^{\circ}\text{C}, R_L = 100 \text{k}\Omega$ $V_O = \pm 0.6\text{V}, R_L = 10 \text{k}\Omega$	25k		25k	
Supply Current	$T_A = 25^{\circ}\text{C}$		8 μA		90 μA
Power Consumption	$T_A = 25^{\circ}\text{C}$		24 μW		270 μW
V_{OS}	$R_S \leq 10 \text{k}\Omega$		7.5 mV		7.5 mV
I_{OS}			8 nA		25 nA
I_{bias}			10 nA		80 nA
Input Voltage Range		$\pm 0.6\text{V}$		$\pm 0.6\text{V}$	
Large Signal Voltage Gain	$V_O = \pm 0.5\text{V}, R_L = 100 \text{k}\Omega$ $R_L = 10 \text{k}\Omega$	25k		25k	
Output Voltage Swing	$R_L = 100 \text{k}\Omega$ $R_L = 10 \text{k}\Omega$	$\pm 0.6\text{V}$		$\pm 0.6\text{V}$	
Common Mode Rejection Ratio	$R_S \leq 10 \text{k}\Omega$	70 dB		70 dB	
Supply Voltage Rejection Ratio	$R_S \leq 10 \text{k}\Omega$	65 dB		65 dB	
Supply Current			8 μA		90 μA
Power Consumption			24 μW		270 μW

ELECTRICAL CHARACTERISTICS ($-55^{\circ}\text{C} \leq T_A \leq +125^{\circ}\text{C}$ unless otherwise specified) (Continued)

Parameters	Conditions	$V_S = \pm 15\text{V}$			
		$I_{SET} = 1 \mu\text{A}$		$I_{SET} = 10 \mu\text{A}$	
		Min	Max	Min	Max
V_{OS}	$T_A = 25^{\circ}\text{C}, R_S \leq 100 \text{k}\Omega$		6 mV		6 mV
I_{OS}	$T_A = 25^{\circ}\text{C}$		6 nA		20 nA
I_{bias}	$T_A = 25^{\circ}\text{C}$		10 nA		75 nA
Large Signal Voltage Gain	$T_A = 25^{\circ}\text{C}, R_L = 100 \text{k}\Omega$ $V_O = \pm 0.6\text{V}, R_L = 10 \text{k}\Omega$	60k		60k	
Supply Current	$T_A = 25^{\circ}\text{C}$		11 μA		100 μA
Power Consumption	$T_A = 25^{\circ}\text{C}$		330 μW		3 mW
V_{OS}	$R_S \leq 10 \text{k}\Omega$		7.5 mV		7.5 mV
I_{OS}			8 nA		25 nA
I_{bias}			10 nA		80 nA
Input Voltage Range		$\pm 13.5\text{V}$		$\pm 13.5\text{V}$	
Large Signal Voltage Gain	$V_O = \pm 10\text{V}, R_L = 100 \text{k}\Omega$ $R_L = 10 \text{k}\Omega$	50k		50k	
Output Voltage Swing	$R_L = 100 \text{k}\Omega$ $R_L = 10 \text{k}\Omega$	$\pm 12\text{V}$		$\pm 12\text{V}$	
Common Mode Rejection Ratio	$R_S \leq 10 \text{k}\Omega$	70 dB		70 dB	
Supply Voltage Rejection Ratio	$R_S \leq 10 \text{k}\Omega$	74 dB		74 dB	
Supply Current			11 μA		100 μA
Power Consumption			300 μW		3 mW